Sheet 1 of 1

F	ORM F	PTO-1449			ATTY. DOCKET NO.		APPLICATION NO.	CONFIRMATI	ION NO
LIST OF PATENTS AND PUBLICATIONS FOR					10007804-1 APPLICANT			<u></u>	
		ANT'S INFORMAT	ION DISCLOSURE		Kuo, et al.				
STATEMENT (Use several sheets if necessary)					FILING DATE GROUP				
					Sept 4, 2003				
REFERE	NCE	DESIGNATION	U.S. P/	ATEN	T DOCUMENTS				
EXAMINE INITIAL			PUBLICATION DATE		NAME		Pages, Columns, Lines Where Relevant Passages or Figures Appear		
A.	1A	5,981,303	11/09/99	Gil	Gilton				
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	11	DOCUMENT NUMBER	PUBLICATION DATE	N	AME OF PATENTEE OR APPLICANT		Pages/Columns/Line evant Passages/Figu		Check in Translation attached
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	<u></u>	OTHER REF	ERENCES (including	ng Au	thor, Title, Date, P	ertine	nt Pages, etc.)	<del></del>	<del></del>
	110	Halimaoui; Po	orous Silicon: Materi	al pro	cessing, properties a	nd apr	olications.: Porou	s Silicon	
$\Rightarrow$	'	Science and T	echnology; (1994)	Leċtur	cessing, properties ar e 3	• •	·		
70									
IR Sheng, et al.; Improved cold electron emission characteristics of electroluminesce diodes; J. Vac. Science Technology (1997); pgs. 1661-1665									
SPP		diodes; J. Va	c. Science Technolo	gy (19	997); pgs. 1661-1665 -	5	-	•	
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	18	Sheng, et al.: Efficient and ballistic cold electron emission from porous polycovstalline silicon							
fe	Sheng, et al.; Efficient and ballistic cold electron emission from porous polycrystalline silicon diodes with a porosity multilayer structure; J. Vac. Science Technology; (2001) pgs 64-67								
EXAM	EXAMINER				DATE CONSIDER			<del></del>	
	9	Course	egla		}		2/9/05		
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